

L Number	Hits	Search Text	DB	Time stamp
82	2	("6674667").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:02
83	3	"20020110033" or ("6674667").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:02
81	2	"20020110033"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:02
84	12725	metal adj oxide adj semiconductor adj field adj effect adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:04
87	3	apply\$6 adj2 third adj voltage near1 potential adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:05
88	3	apply\$6 adj2 third adj3 voltage near1 potential adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:15
85	5	apply\$6 adj2 first adj voltage near1 potential adj3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:08
86	6	apply\$6 adj2 second adj voltage near1 potential adj3 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:12
89	5	(apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:12
90	4	((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:13
91	1	((((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel) and negative adj gate adj1 potential near3 conduction adj1 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:14
92	1	((((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel) and negative adj gate adj1 potential	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:14
94	0	apply\$6 adj2 negative adj3 voltage near1 potential adj3 gate near5 MOSFet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:15
95	5	apply\$6 adj2 negative adj3 voltage near1 potential adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:49
97	18	("4,051,354") or ("5,324,681") or ("5,327,380") or ("5,493,141") or ("5,764,096") or ("5,768,192") or ("5,781,477") or ("6,038,168") or ("6,229,733")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:20
98	809	apply\$6 adj2 negative adj3 voltage adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:49

99	4802	apply\$6 adj2 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:49
100	4802	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:50
101	1039	(apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate) and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:50
102	260	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:50
104	103	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	US-PGPUB; EPO; JPO; DERWENT	2004/03/21 14:51
103	157	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	USPAT	2004/03/21 14:51
105	150	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet	USPAT	2004/03/21 14:53
106	150	apply adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet	USPAT	2004/03/21 14:52
107	150	appl\$ adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet	USPAT	2004/03/21 14:54
108	30	(appl\$ adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj1 voltage adj3 gate near5 mosfet) and negative adj1 voltage	USPAT	2004/03/21 14:54